

ABSTRACT OF THE DISCLOSURE

It is intended to provide a semiconductor memory device capable of making margin of readout operation constant regardless
5 of any selected memory cells wherein the number of reference cells is restrained to minimum essential number and reference current value of which depends on a selected memory cell is obtained. A memory cell selected by address $Y(X)$ is connected to a data line DB and data in the memory cell is read out from a
10 memory cell array 3. Then, a differential amplifier 4 amplifies the data with reference to a reference value supplied to a reference line RB from a reference section 2. The reference section 2 is constituted by a reference cell RC and a source resistance adjustor section 1 that is connected to a source
15 terminal of the reference cell RC. A load adjustor section 1 adjusts a resistance value that is connected to the source terminal of the reference cell RC by the address $Y(X)$. A source resistance adjustor section 1 connects a load equivalent to a load selected by a memory cell in accordance with the address
20 $Y(X)$ to the reference cell RC, whereby an appropriate reference value is constantly supplied.